



SIE854DF-T1-GE3 Information



For Reference Only

Part Number SIE854DF-T1-GE3
Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 100V 60A POLARPAK

Package 10-PolarPAK? (L)

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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Certified Quality

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SIE854DF-T1-GE3 Specifications

Manufacturer Part Number SIE854DF-T1-GE3 Manufacturer Vishay Siliconix Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 10-PolarPAK? (L) Series TrenchFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 60A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4.4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 75nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3100pF @ 50V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 5.2W (Ta), 125W (Tc) Rds On (Max) @ Id, Vgs 14.2 mOhm @ 13.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PolarPAK? (L) Package / Case 10-PolarPAK? (L)		
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Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.4V @ 250μAGate Charge (Qg) (Max) @ Vgs75nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3100pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)5.2W (Ta), 125W (Tc)Rds On (Max) @ Id, Vgs14.2 mOhm @ 13.2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package10-PolarPAK? (L)Package / Case10-PolarPAK? (L)	Drain to Source Voltage (Vdss)	100V
Vgs(th) (Max) @ Id 4.4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 75nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3100pF @ 50V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 5.2W (Ta), 125W (Tc) Rds On (Max) @ Id, Vgs 14.2 mOhm @ 13.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PolarPAK? (L) Package / Case 10-PolarPAK? (L)	Current - Continuous Drain (Id) @ 25°C	60A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 14.2 mOhm @ 13.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PolarPAK? (L) Package / Case	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 14.2 mOhm @ 13.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PolarPAK? (L) Package / Case	Vgs(th) (Max) @ Id	4.4V @ 250μA
Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 5.2W (Ta), 125W (Tc) Rds On (Max) @ Id, Vgs 14.2 mOhm @ 13.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PolarPAK? (L) Package / Case 10-PolarPAK? (L)	Gate Charge (Qg) (Max) @ Vgs	75nC @ 10V
FET Feature - Power Dissipation (Max) 5.2W (Ta), 125W (Tc) Rds On (Max) @ Id, Vgs 14.2 mOhm @ 13.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PolarPAK? (L) Package / Case 10-PolarPAK? (L)	Input Capacitance (Ciss) (Max) @ Vds	3100pF @ 50V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 14.2 mOhm @ 13.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PolarPAK? (L) Package / Case	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs14.2 mOhm @ 13.2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package10-PolarPAK? (L)Package / Case10-PolarPAK? (L)	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PolarPAK? (L) Package / Case 10-PolarPAK? (L)	Power Dissipation (Max)	5.2W (Ta), 125W (Tc)
Mounting Type Surface Mount Supplier Device Package 10-PolarPAK? (L) Package / Case 10-PolarPAK? (L)	Rds On (Max) @ Id, Vgs	14.2 mOhm @ 13.2A, 10V
Supplier Device Package 10-PolarPAK? (L) Package / Case 10-PolarPAK? (L)	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case 10-PolarPAK? (L)	Mounting Type	Surface Mount
	Supplier Device Package	10-PolarPAK? (L)
Report errors?	Package / Case	10-PolarPAK? (L)
		Report errors?

SIE854DF-T1-GE3 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

SIE854DF-T1-GE3 Payment Methods









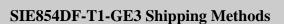
























If you have any question about SIE854DF-T1-GE3, please do not hesitate to contact us!

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